

## isc Silicon NPN Darlington Power Transistor

2SD1827

## DESCRIPTION

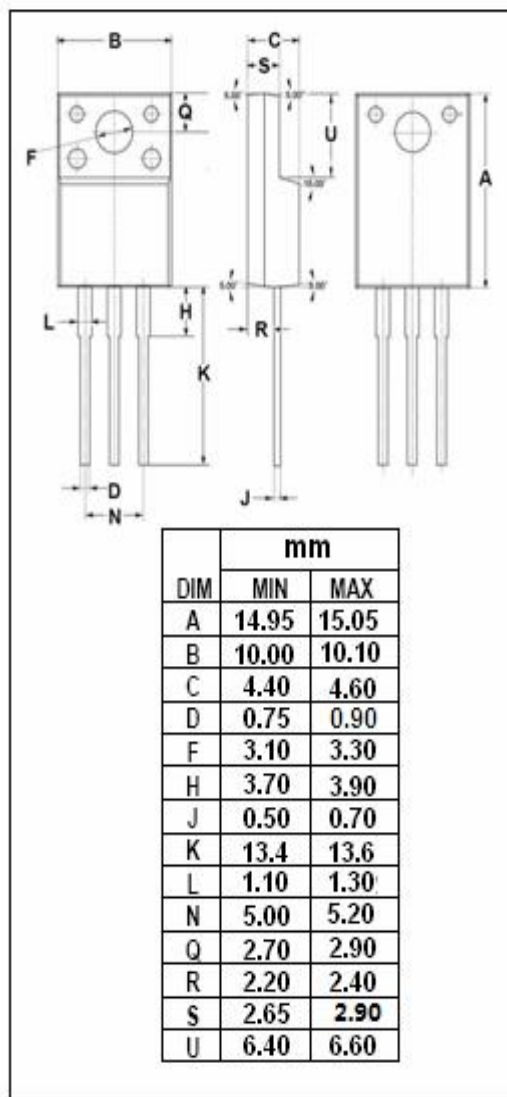
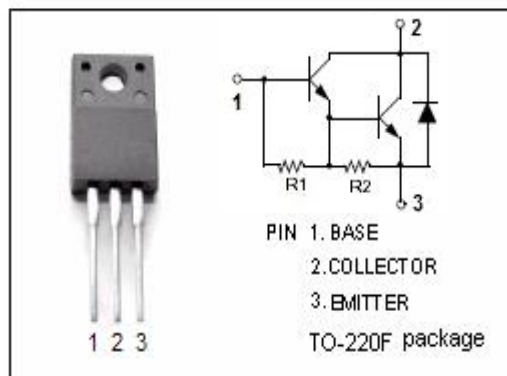
- High DC Current Gain-  
:  $h_{FE} = 2000(\text{Min}) @ (V_{CE} = 2V, I_C = 5A)$
- Large Current Capability and Wide ASO.
- Complement to Type 2SB1225
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

- Designed for use in control of motor drivers, printer hammer drivers, relay drivers, and constant-voltage regulators.

ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	70	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	10	A
$I_{CM}$	Collector Current-Peak	15	A
$P_C$	Collector Power Dissipation @ $T_a = 25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	30	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



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## ELECTRICAL CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; R <sub>BE</sub> = ∞	60			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 5mA; I <sub>E</sub> = 0	70			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 10mA			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 10mA			2.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 40V; I <sub>E</sub> = 0			100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			3.0	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 2V	2000	5000		
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V		20		MHz

## Switching Times

t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 5A, I <sub>B1</sub> = -I <sub>B2</sub> = 10mA, V <sub>CC</sub> = 20V; R <sub>L</sub> = 4 Ω		0.6		μ s
t <sub>stg</sub>	Storage Time			3.0		μ s
t <sub>f</sub>	Fall Time			1.8		μ s

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